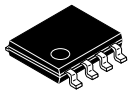
Single-Channel High-Side Gate Drive IC

FAN73611



SOIC8
(8−SOP)
CASE 751EG

Description

The FAN73611 is a monolithic high−side gate drive IC that can drive MOSFETs and IGBTs operating up to +600 V. **onsemi**'s high−voltage process and commonmode noise canceling techniques provide stable operation of the high−side driver under high dv/dt noise circumstances. An advanced level−shift circuit offers high−side gate driver operation up to V_S = −9.8 V (typical) for V_{BS} = 15 V. The UVLO circuits prevents malfunction when V_{DD} or V_{BS} is lower than the specified threshold voltage. The output drivers typically source/sink 250 mA/500 mA; respectively, which is suitable for Plasma Display Panel (PDP) application, motor drive inverter, and switching mode power supply applications.

Features

- Floating Channel of Bootstrap Operation to +600 V
- 250 mA / 500 mA Sourcing/Sinking Current Driving Capability
- Common−Mode dv/dt Noise−Cancelling Circuit
- 3.3 V and 5 V Input Logic Compatible
- Output In Phase with Input Signal
- Under−Voltage Lockout for V_{DD} and V_{BS}
- 8−Lead Small Outline Package (SOP)
- This is a Pb−Free Device

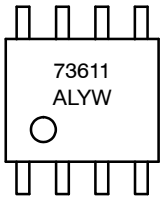
Applications

- Electronic Ballast
- Switching−Mode Power Supply (SMPS)

Related Resources

- AN−6076 – Design and Application Guide of Bootstrap Circuit for High−Voltage Gate−Drive IC
- AN−9052 – Design Guide for Selection of Bootstrap Components
- AN−8102 – Recommendations to Avoid Short Pulse Width Issues in HVIC Gate Driver Applications

MARKING DIAGRAM



73611 = Device Code
A = Assembly Site
L = Wafer Lot Number
YW = Assembly Start Week

ORDERING INFORMATION

See detailed ordering and shipping information on page 11 of this data sheet.

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TYPICAL APPLICATION DIAGRAMS

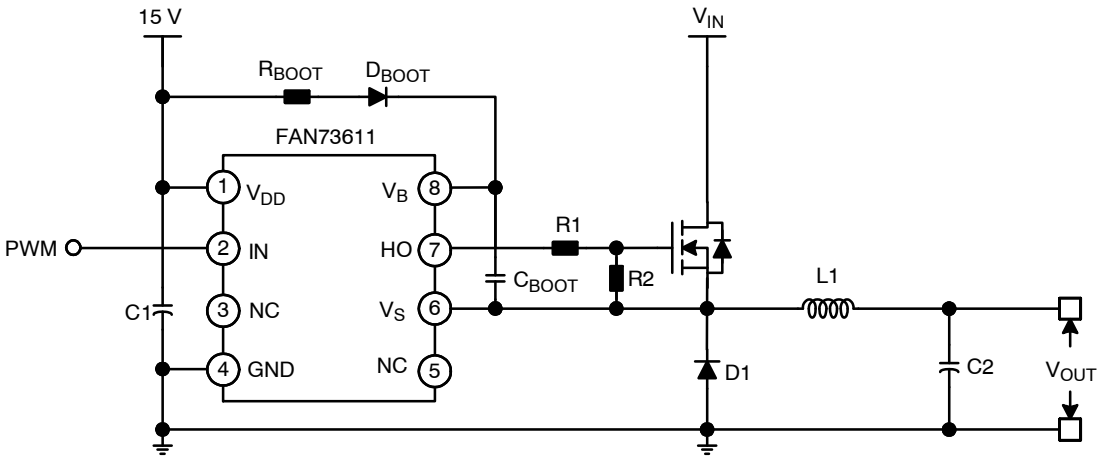


Figure 1. Step−Down (Buck) DC−DC Converter Application

INTERNAL BLOCK DIAGRAM

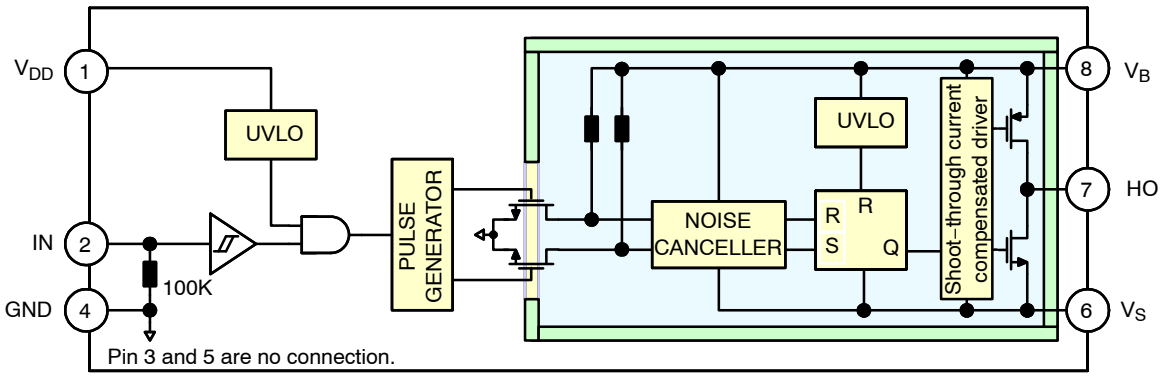


Figure 2. Functional Block Diagram

PIN CONFIGURATION

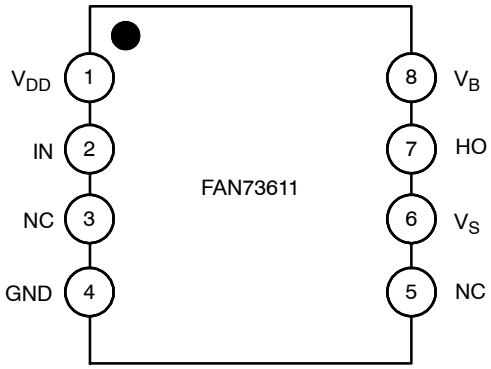


Figure 3. Pin Configuration (Top View)

PIN DEFINITIONS

Pin No.	Name	Description
1	V_{DD}	Supply Voltage
2	IN	Logic Input for High−Side Gate Driver Output
3	NC	No Connection
4	GND	Ground
5	NC	No Connection
6	V_S	High−Voltage Floating Supply Return
7	HO	High−Side Driver Output
8	V_B	High−Side Floating Supply

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C, unless otherwise specified.)

Symbol	Parameter	Min	Max	Unit
V_S	High−Side Floating Offset Voltage	V_B − 25	V_B + 0.3	V
V_B	High−Side Floating Supply Voltage	−0.3	625.0	V
V_{HO}	High−Side Floating Output Voltage	V_S − 0.3	V_B + 0.3	V
V_{DD}	Low−Side and Logic Supply Voltage	−0.3	25.0	V
V_{IN}	Logic Input Voltage	−0.3	V_{DD} + 0.3	V
dV_S/dt	Allowable Offset Voltage Slew Rate	−	±50	V/ns
P_D	Power Dissipation (Notes 1, 2, 3)	−	0.625	W
θ_{JA}	Thermal Resistance	−	200	°C/W
T_J	Junction Temperature	−55	+150	°C
T_{STG}	Storage Temperature	−55	+150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Mounted on 76.2 x 114.3 x 1.6 mm PCB (FR−4 glass epoxy material).
2. Refer to the following standards:
   JESD51−2: Integral circuits thermal test method environmental conditions, natural convection, and
   JESD51−3: Low effective thermal conductivity test board for leaded surface mount packages
3. Do not exceed power dissipation (P_D) under any circumstances.

RECOMMENDED OPERATING RATINGS

Symbol	Parameter	Min	Max	Unit
V_B	High−Side Floating Supply Voltage	V_S + 10	V_S + 20	V
V_S	High−Side Floating Supply Offset Voltage	6 − V_{DD}	600	V
V_{HO}	High−Side Output Voltage	V_S	V_B	V
V_{IN}	Logic Input Voltage	GND	V_{DD}	V
V_{DD}	Supply Voltage	10	20	V
T_A	Operating Ambient Temperature	−40	+125	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

ELECTRICAL CHARACTERISTICS (V_{BIAS} (V_{DD}, V_{BS}) = 15.0 V and T_A = 25°C unless otherwise specified. The V_{IN} and I_{IN} parameters are referenced to GND. The V_O and I_O parameters are relative to V_S and are applicable to the respective outputs HO.)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
POWER SUPPLY SECTION						
I_{QDD}	Quiescent V_{DD} Supply Current	V_{IN} = 0 V or 5 V, C_{LOAD} = 1000 pF	–	80	140	μA
I_{PDD}	Operating V_{DD} Supply Current	C_{LOAD} = 1000 pF, f_{IN} = 20 kHz, RMS value	–	80	160	μA
V_{DDUV+} V_{BSUV+}	V_{DD} and V_{BS} Supply Under−Voltage Positive Going Threshold Voltage	V_{DD} = Sweep, V_{BS} = Sweep	7.8	8.8	9.8	V
$V_{DDUV−}$ $V_{BSUV−}$	V_{DD} and V_{BS} Supply Under−Voltage Negative Going Threshold Voltage	V_{DD} = Sweep, V_{BS} = Sweep	7.3	8.3	9.3	V
V_{DDHYS} V_{BSHYS}	V_{DD} and V_{BS} Supply Under−Voltage Lockout Hysteresis Voltage	V_{DD} = Sweep, V_{BS} = Sweep	–	0.5	–	V
I_{LK}	Offset Supply Leakage Current	V_B = V_S = 600 V	–	–	10	μA
I_{QBS}	Quiescent V_{BS} Supply Current	V_{IN} = 0 V or 5 V, C_{LOAD} = 1000 pF		60	100	μA
I_{PBS}	Operating V_{BS} Supply Current	C_{LOAD} = 1000 pF, f_{IN} = 20 kHz, RMS value		420	600	μA
INPUT LOGIC SECTION						
V_{IH}	Logic “1” Input Voltage		2.5	–	–	V
V_{IL}	Logic “0” Input Voltage		–	–	0.8	V
I_{IN+}	Logic Input High Bias Current	V_{IN} = 5 V	–	50	75	μA
$I_{IN−}$	Logic Input Low Bias Current	V_{IN} = 0 V	–	–	2	μA
R_{IN}	Input Pull−Down Resistance		60	100	–	kΩ
GATE DRIVE OUTPUT SECTION						
V_{OH}	High Level Output Voltage (V_{BIAS} − V_O)	No Load	–	–	0.1	V
V_{OL}	Low Level Output Voltage	No Load	–	–	0.1	V
I_{O+}	Output High, Short−Circuit Pulsed Current	V_{HO} = 0 V, V_{IN} = 5 V, PW ≤ 10 μs	200	250	–	mA
$I_{O−}$	Output Low, Short−Circuit Pulsed Current	V_{HO} = 15 V, V_{IN} = 0 V, PW ≤ 10 μs	400	500	–	mA
V_S	Allowable Negative V_S Pin Voltage for IN Signal Propagation to HO	V_{BS} = 15 V	–	−9.8	−7.0	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

DYNAMIC ELECTRICAL CHARACTERISTICS (V_{DD} = V_{BS} = 15 V, C_{LOAD} = 1000 pF, and T_A = 25°C, unless otherwise specified.)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
t_{on}	Turn−on Propagation Delay Time	V_S = 0 V	70	120	170	ns
t_{off}	Turn−off Propagation Delay Time	V_S = 0 V	70	120	170	ns
t_r	Turn−on Rise Time		–	70	140	ns
t_f	Turn−off Fall Time		–	30	60	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

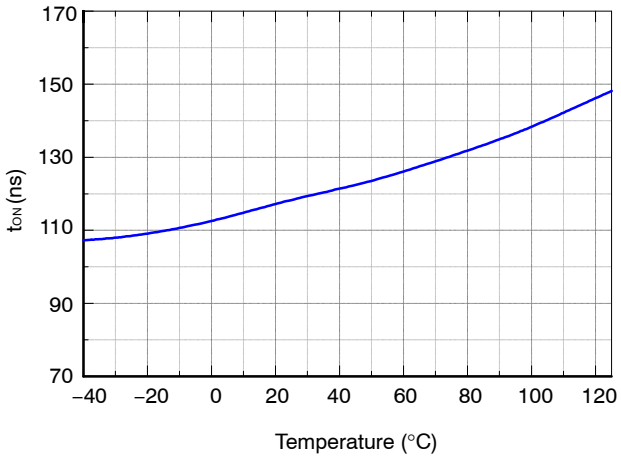


Figure 4. Turn−On Propagation Delay vs. Supply Voltage

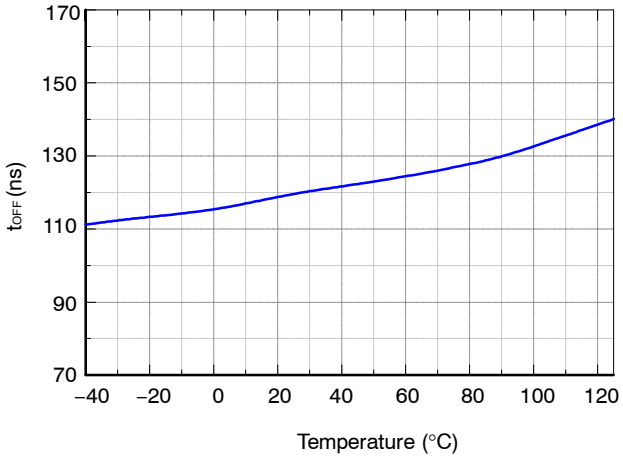


Figure 5. Turn−Off Propagation Delay vs. Temperature

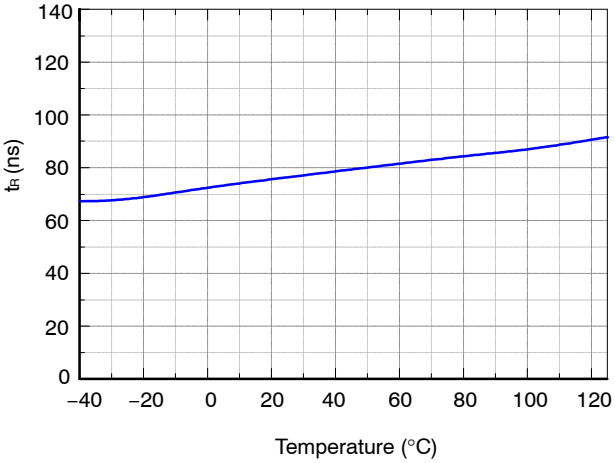


Figure 6. Turn−On Rise Time vs. Temperature

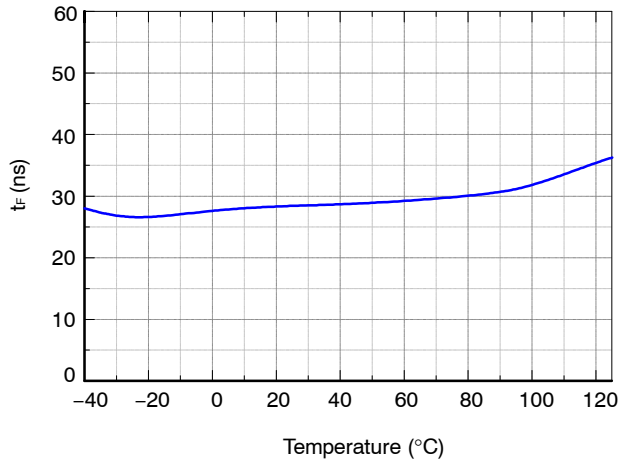


Figure 7. Turn−Off Fall Time vs. Temperature

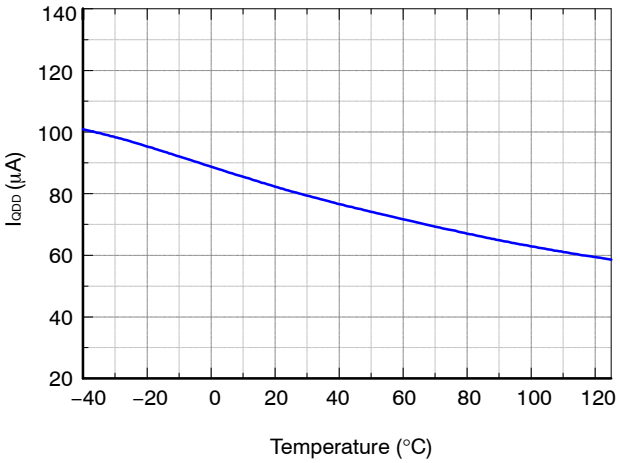


Figure 8. Quiescent V_{DD} Supply Current vs. Temperature

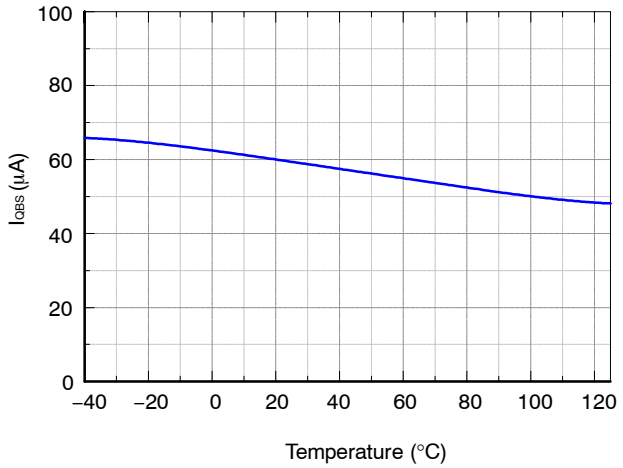


Figure 9. Quiescent V_{BS} Supply Current vs. Temperature

TYPICAL CHARACTERISTICS (Continued)

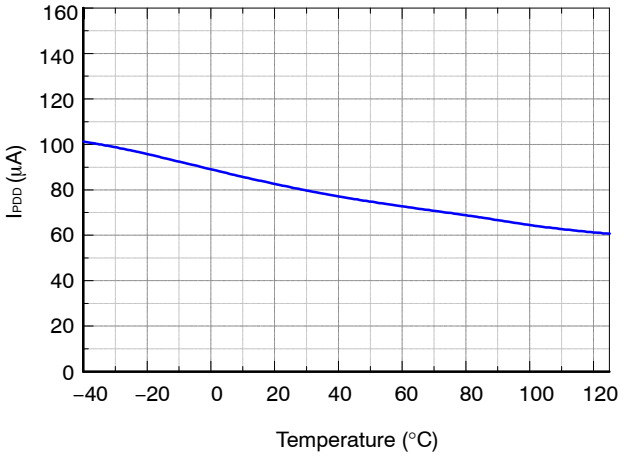


Figure 10. Operating V_{DD} Supply Current vs. Temperature

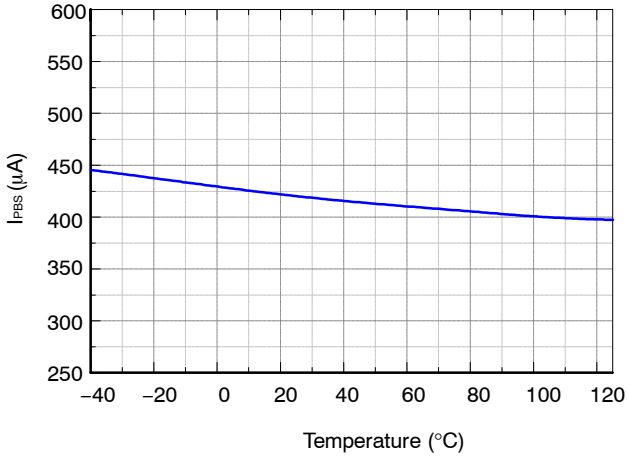


Figure 11. Operating V_{BS} Supply Current vs. Temperature

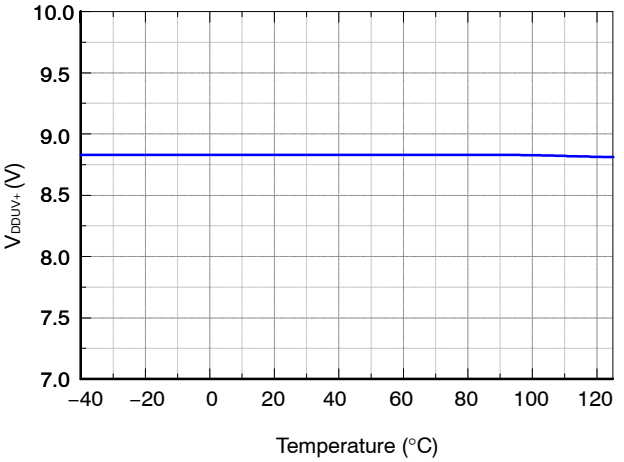


Figure 12. V_{DD} UVLO+ vs. Temperature

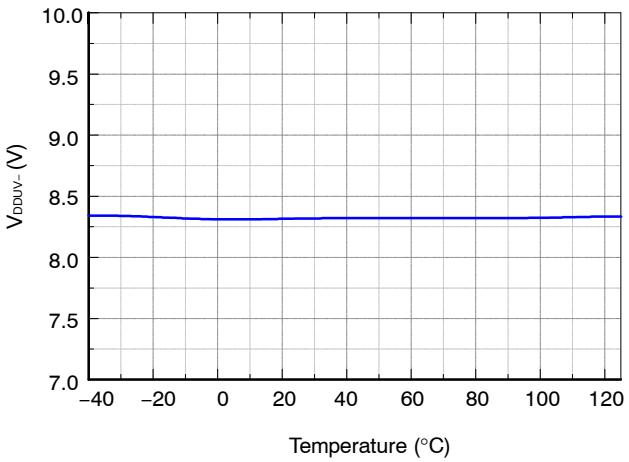


Figure 13. V_{DD} UVLO− vs. Temperature

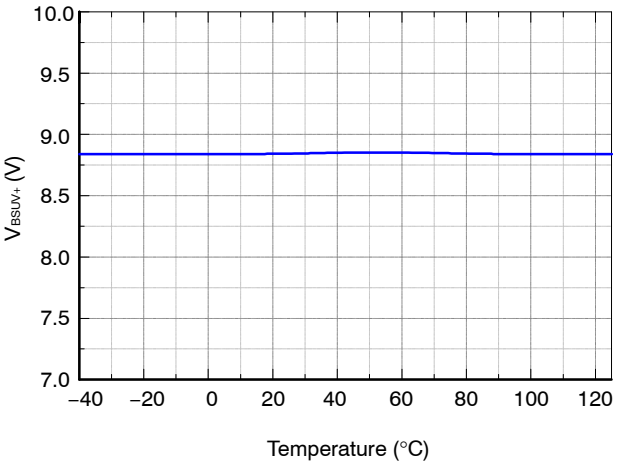


Figure 14. V_{BS} UVLO+ vs. Temperature

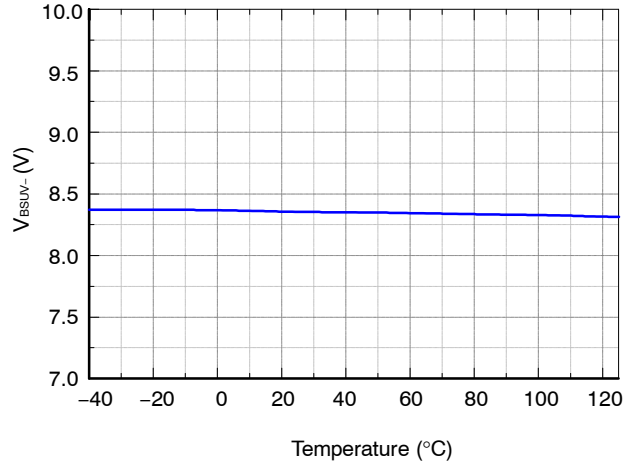


Figure 15. V_{BS} UVLO− vs. Temperature

TYPICAL CHARACTERISTICS (Continued)

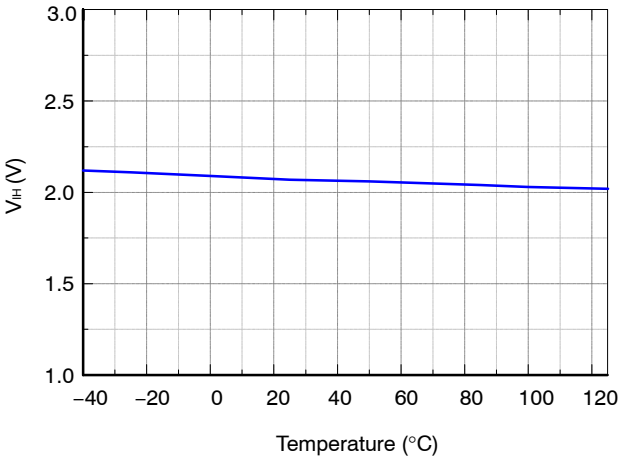


Figure 16. Logic HIGH Input Voltage vs. Temperature

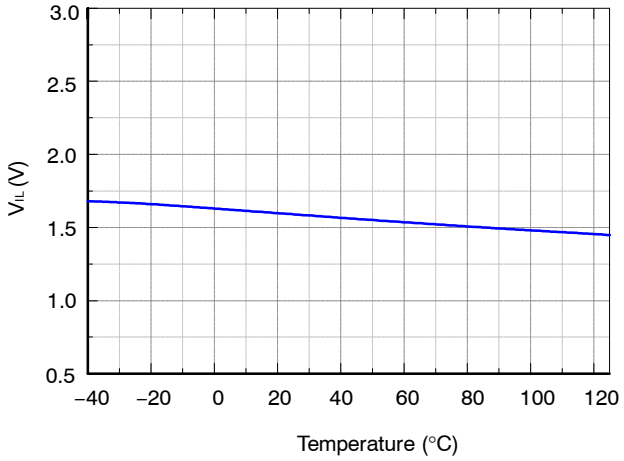


Figure 17. Logic LOW Input Voltage vs. Temperature

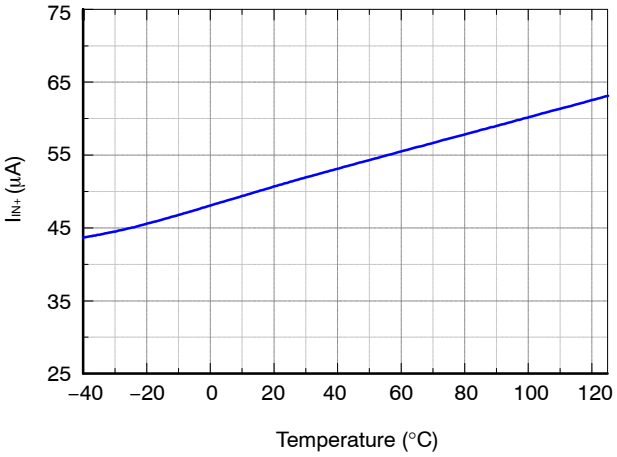


Figure 18. Logic HIGH Input Bias Current vs. Temperature

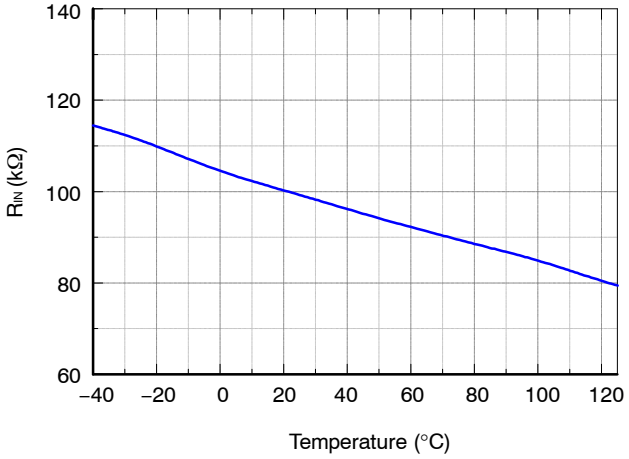


Figure 19. Input Pull−Down Resistance vs. Temperature

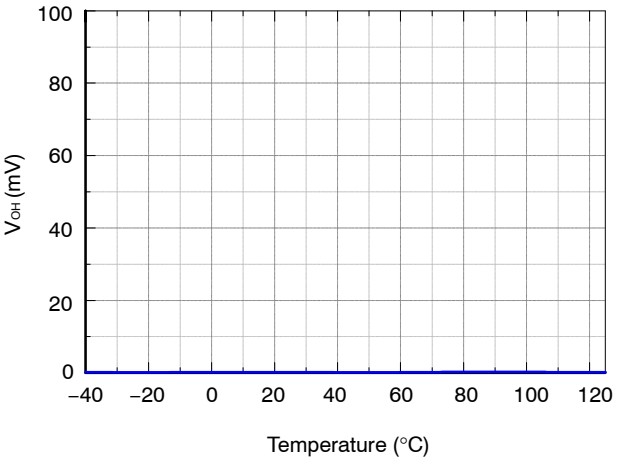


Figure 20. High−Level Output Voltage vs. Temperature

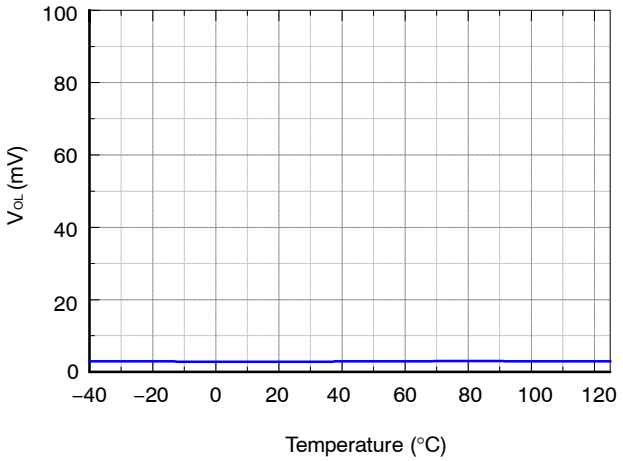


Figure 21. Low−Level Output Voltage vs. Temperature

TYPICAL CHARACTERISTICS (Continued)

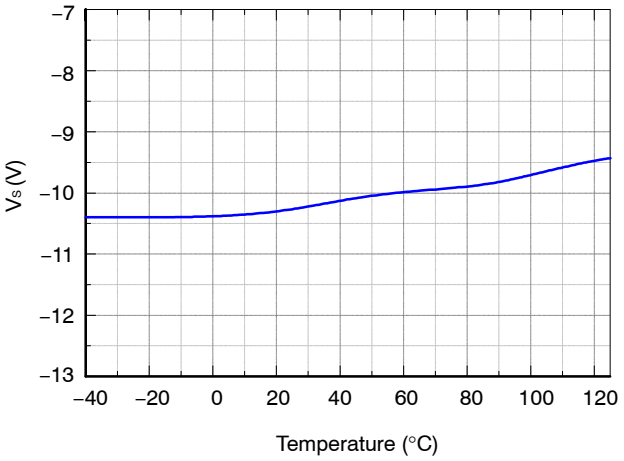


Figure 22. Allowable Negative V_S Voltage vs. Temperature

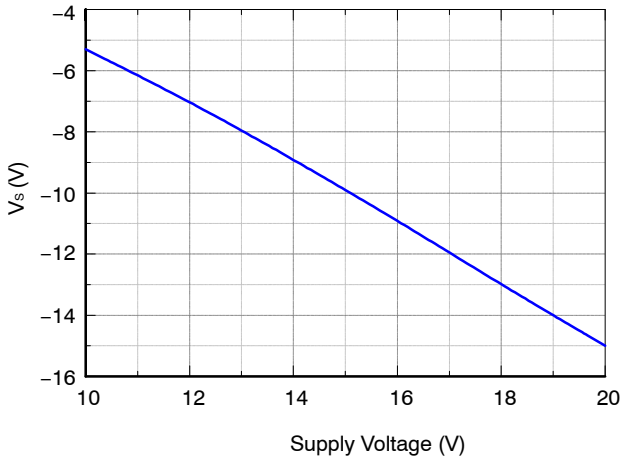


Figure 23. Allowable Negative V_S Voltage vs. Supply Voltage

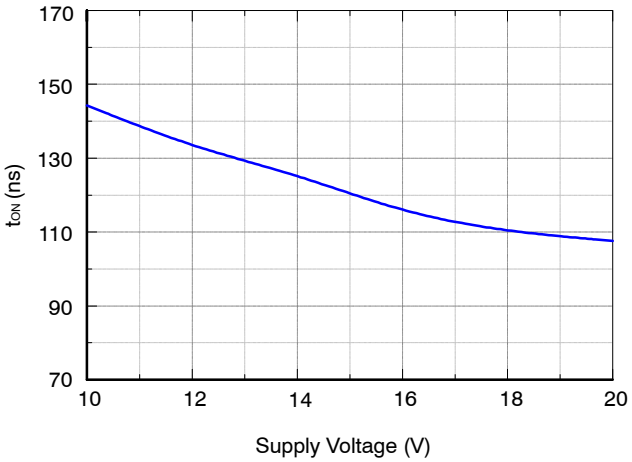


Figure 24. Turn−On Propagation Delay vs. Supply Voltage

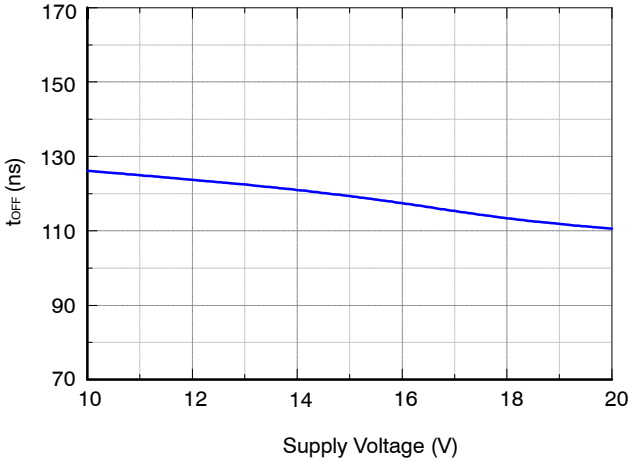


Figure 25. Turn−Off Propagation Delay vs. Supply Voltage

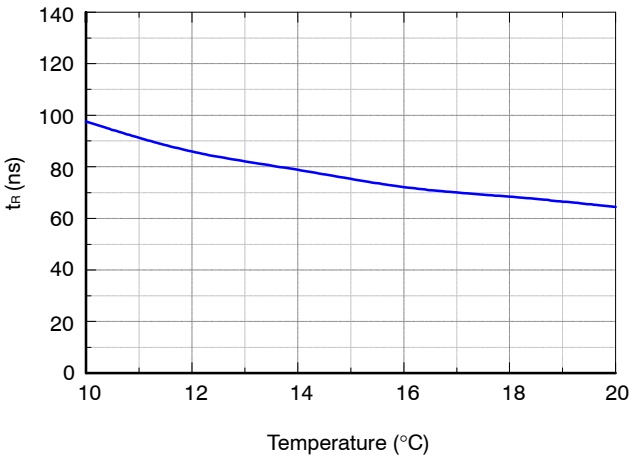


Figure 26. Turn−On Rise Time vs. Supply Voltage

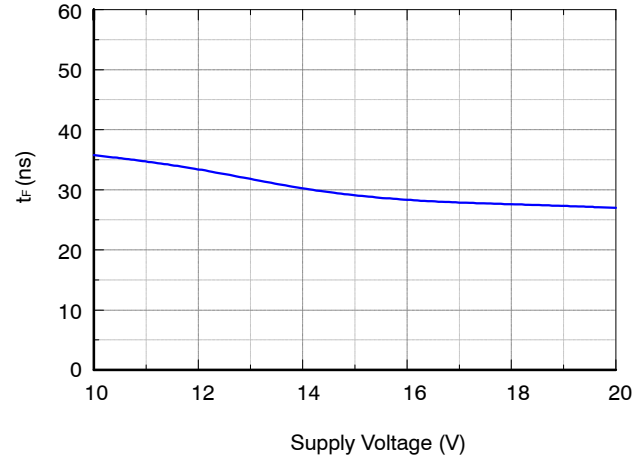


Figure 27. Turn−Off Fall Time vs. Supply Voltage

TYPICAL CHARACTERISTICS (Continued)

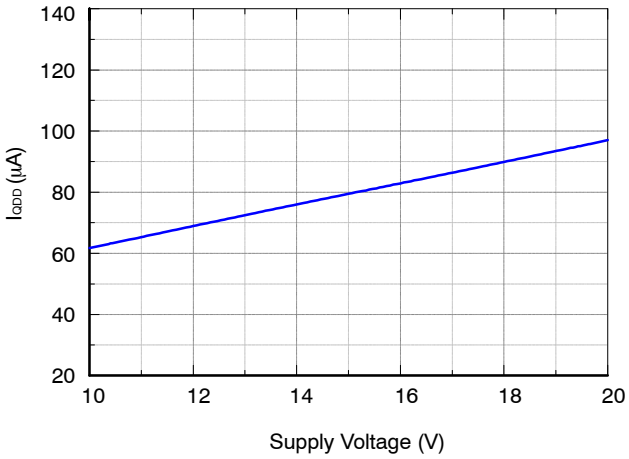


Figure 28. Quiescent V_{DD} Supply Current vs. Supply Voltage

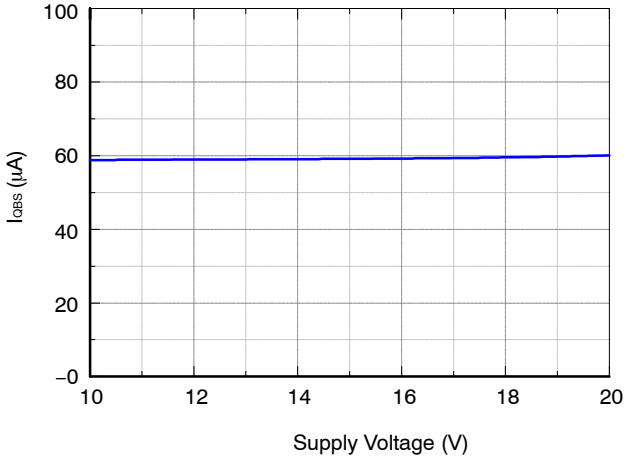


Figure 29. Quiescent V_{BS} Supply Current vs. Supply Voltage

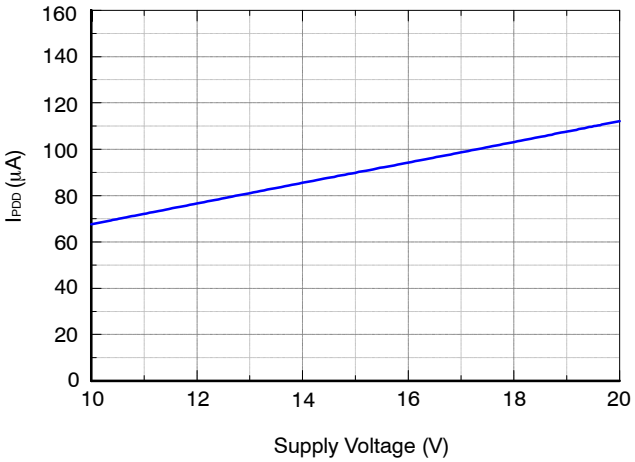


Figure 30. Operating V_{DD} Supply Current vs. Supply Voltage

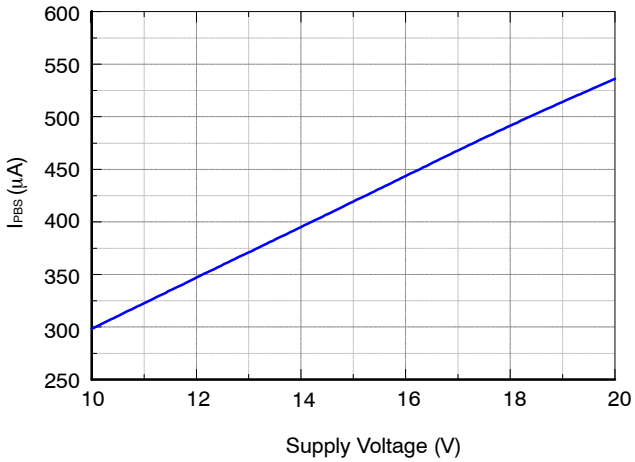


Figure 31. Operating V_{DD} Supply Current vs. Supply Voltage

SWITCHING TIME DEFINITIONS

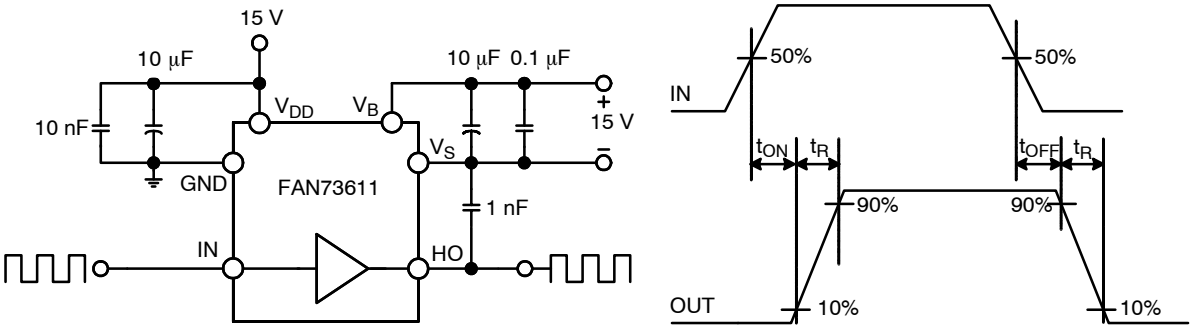


Figure 32. Switching Time Test Circuit and Waveforms Definitions

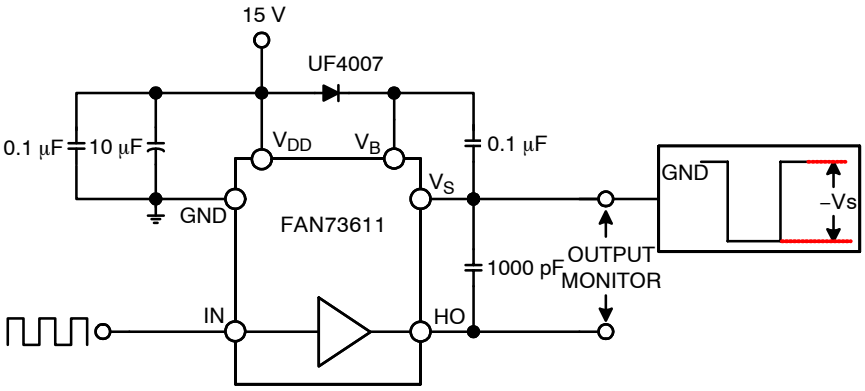


Figure 33. Floating Supply Voltage Transient Test

ORDERING INFORMATION

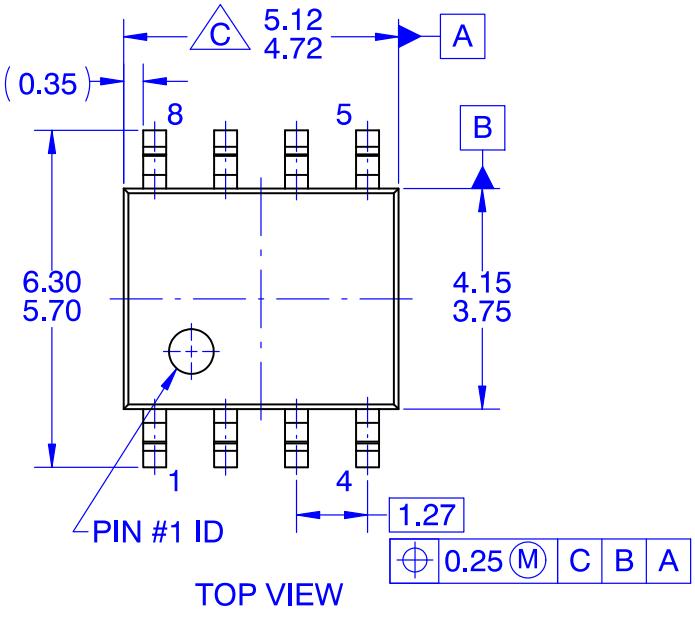
Device	Package	Operating Temperature	Description	Shipping†
FAN73611MX (Note 4)	SOIC8 (8−SOP) (Pb−Free)	−40°C~+125°C	Lightning Application	3000 / Tape & Reel

4. This device has passed wave soldering test by JESD22A−111.

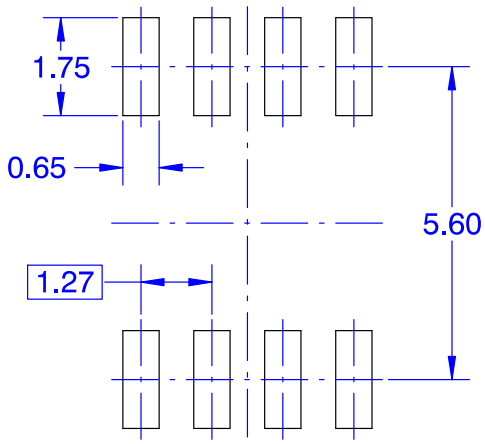
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

SOIC8
CASE 751EG
ISSUE O

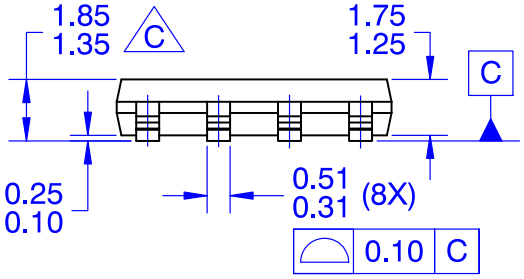
DATE 30 SEP 2016



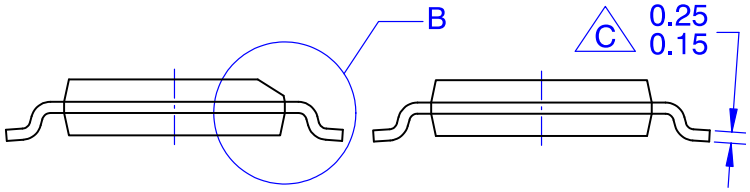
TOP VIEW



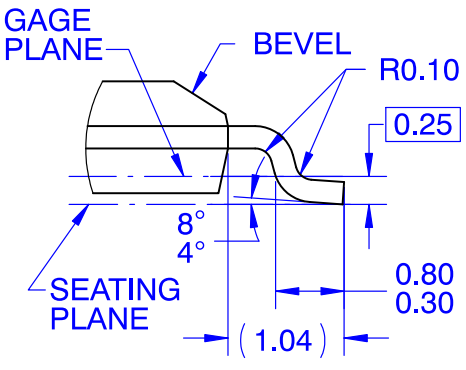
LAND PATTERN RECOMMENDATION



FRONT VIEW



SIDE VIEW



DETAIL "B"
SCALE 2:1

NOTES: UNLESS OTHERWISED SPECIFIED

A. THIS PACKAGE CONFORMS TO JEDEC MS–012 VARIATION A EXCEPT WHERE NOTED.
B. ALL DIMENSIONS ARE IN MILLIMETERS
C OUT OF JEDEC STANDARD VALUE
D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
E. LAND PATTERN AS PER IPC SOIC127P600X175–8M

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DESCRIPTION:	**SOIC8**	**PAGE 1 OF 1**

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